



ORY6 PY6 Y F

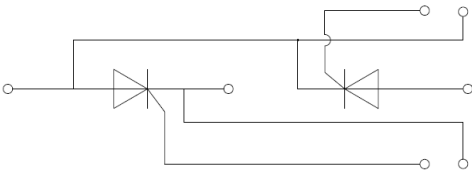
Y R

K f

U X f

Uf f	f	
°C		

F f



Fg Rf Wf

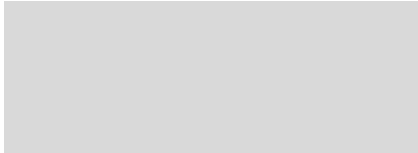
Uf f	H	X g	f	
	°C			
				°C
				°C



J f H f f

Uf f	H	X g	f			
			R 3	Y 3	Rf 3	
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					

Y f H f f



T f

I	R _f	U _f f		G	U _H f

Y f J f Y f H f f

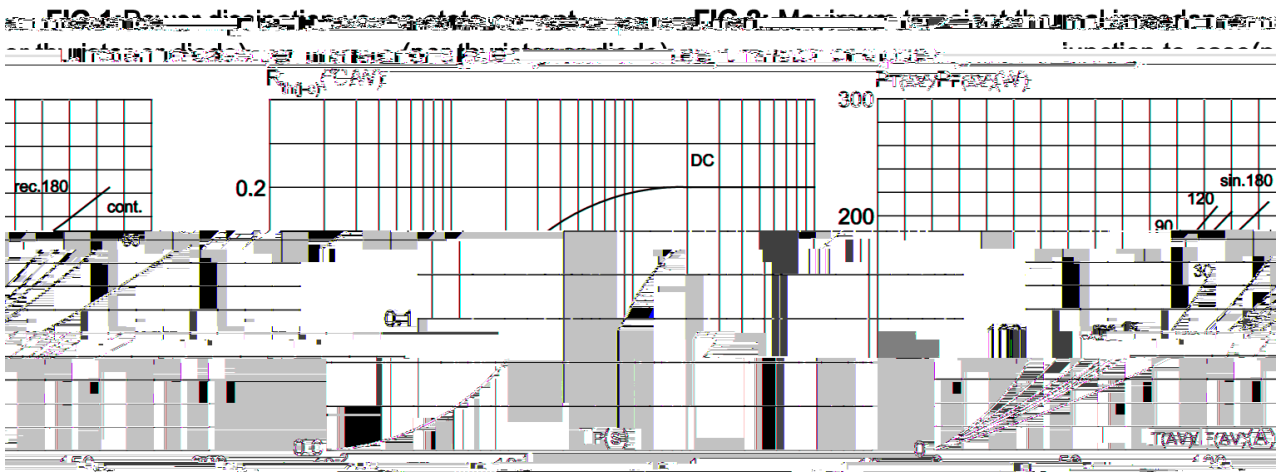


FIG.3: Forward characteristics
(per thyristor or diode)

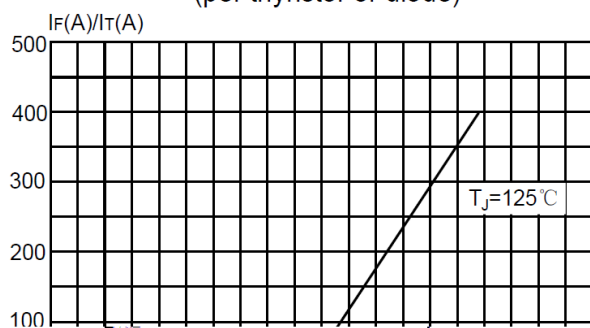


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature
 $I_{GT}, I_H, I_L(T_J)/I_{GT}, I_H, I_L(T_J=25^\circ\text{C})$

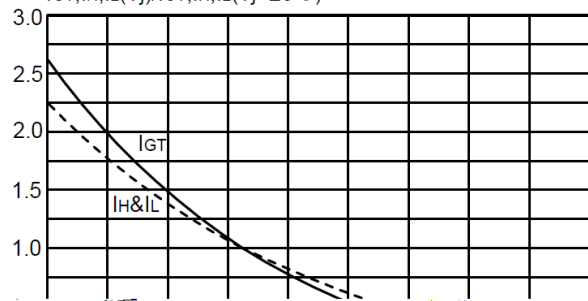


FIG.5: Gate trigger characteristics

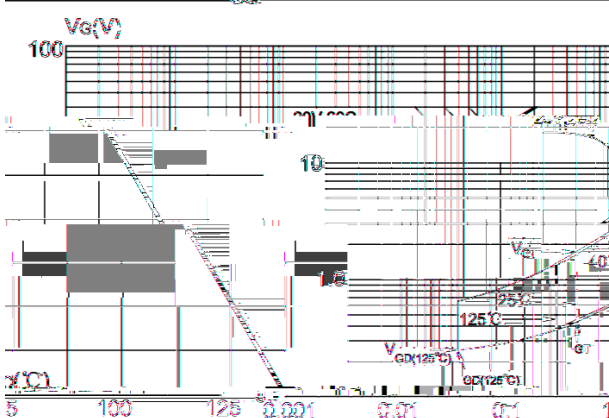
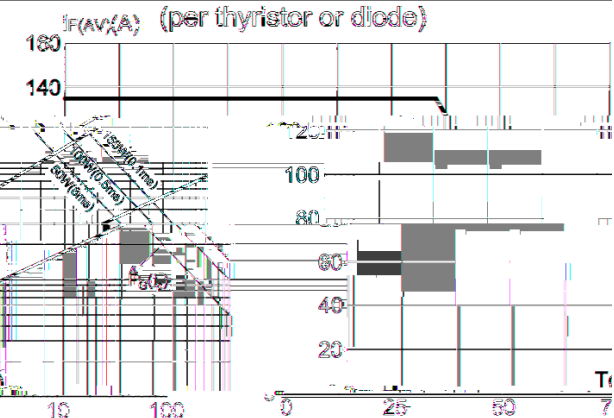


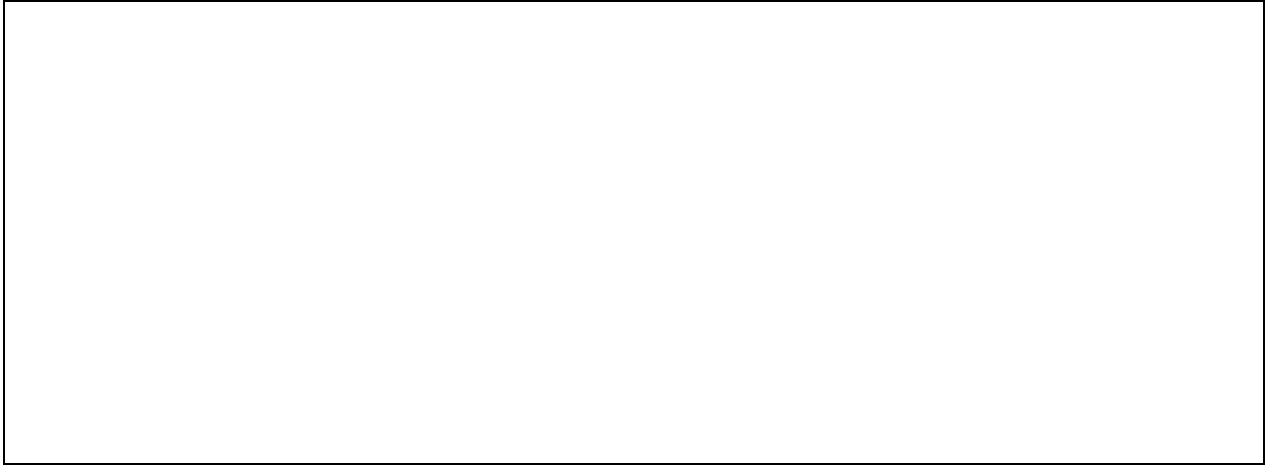
FIG.6: Forward current vs. case temperature





ORY6 PY6 Y F

H I f f



Uf f T .

Uf f T .



ORY6 PY6 Y F